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A semiconductor structure comprising:

an insulator layer formed of a first polymer; and

an organic semiconductor layer formed of a second polymer,

wherein the first and second polymers self-assemble into a well-ordered copolymer structure with the semiconductor layer positioned adjacent the insulator layer.

- 2. The semiconductor structure of claim 1, wherein the co-polymer is a block co-polymer.
- The semiconductor structure of claim 1, wherein the organic semiconductor layer comprises carbon-based nanotubes.
- 4. The semiconductor structure of claim 1, wherein an interface between the insulator layer and the organic semiconductor layer is substantially free of contamination.
- The semiconductor structure of claim 1, wherein the structure is a lamella structure with the insulator and semiconductor layered in parallel.
- 6. The semiconductor structure of claim 1, wherein the structure is a parallel cylindrical structure with parallel cylinders of the organic semiconductor surrounded in a matrix of the insulator.

- 7. The semiconductor structure of claim 1, wherein the structure is a vertically layered cylindrical structure with cylinders of the organic semiconductor surrounded in a matrix of the insulator.
- 8. The semiconductor structure of claim 1, wherein the structure is a lamella structure with the insulator and the semiconductor vertically layered in alternate lamellae of the insulator and the semiconductor.
 - 9. An organic, thin-film semiconductor device comprising:

an insulator layer formed of a first polymer; and

an organic semiconductor layer formed of a second polymer,

wherein the co-polymers self-assemble into a well-ordered co-polymer structure with the semiconductor layer positioned adjacent the insulator layer.

- 10. The semiconductor device of claim 9, wherein the device is a transistor.
- The semiconductor device of claim 10, wherein the transistor is a multi-gate transistor.
- 12. The semiconductor device of claim 9, wherein the device is a thyristor.

CLAIMS 13-20 (CANCELLED)